

145 Adams Avenue, Hauppauge, NY 11788 USA Tel: (631) 435-1110 • Fax: (631) 435-1824

Manufacturers of World Class Discrete Semiconductors

2N4264

NPN SILICON TRANSISTOR JEDEC TO-92 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N4264 type is a Silicon NPN Transistors designed for high speed switching applications.

MAXIMUM RATINGS (TA = 25°C)

	<u>SYMBOL</u>		<u>UNITS</u>
Collector-Base Voltage	$v_{\sf CBO}$	30	V
Collector-Emitter Voltage	V _{CEO}	15	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	^l C	200	mA
Power Dissipation	P_{D}	625	mW
Operating and Storage			
Junction Temperature	T_J, T_stg	-55 to +150	oC
Thermal Resistance	ӨЈА	200	°C/W

ELECTRICAL CHARACTERISTICS $(T_A = 25^{\circ}C)$ unless otherwise noted)

$V_{CE} = 12V$, $V_{BE(OFF)} = 0.25V$ 0.1 $V_{CE} = 12V$, $V_{BE(OFF)} = 0.25V$, $V_{A} = 100^{\circ}$ C 10 $V_{CE} = 1.0$ mA 15	uA uA
02. 02 02 7	
$BV_{CEO} \qquad I_{C} = 1.0 \text{mA} \qquad 15$	
	V
$BV_{CBO} \qquad I_{C} = 10uA, \qquad 20$	V
$BV_{EBO} I_E = 10uA 6.0$	V
$V_{CE(SAT)}$ $I_{C} = 10mA, I_{B} = 1.0mA$ 0.22	V
$V_{CE(SAT)}$ $I_{C} = 100 \text{mA}, I_{B} = 10 \text{mA}$ 0.35	V
$V_{BE(SAT)}$ $I_{C}=10mA$, $I_{B}=1.0mA$ 0.65 0.80	V
$V_{BE(SAT)}$ $I_{C} = 100 \text{mA}, I_{B} = 10 \text{mA}$ 0.75 0.95	V
h_{FE} $V_{CE} = 1.0V, I_{C} = 1.0mA$ 25	-
h_{FE} $V_{CE} = 1.0V, I_{C} = 10mA$ 40 160	-
h_{FE} $V_{CE} = 1.0V, I_{C} = 30mA$ 40	-
h_{FE} $V_{CE} = 1.0V, I_{C} = 100mA$ 30	-
h_{FE} $V_{CE} = 1.0V, I_{C} = 200mA$ 20	-
f_T $V_{CE} = 10V, I_C = 10mA, f = 100MHz$ 350	MHz
$V_{BE} = 0.5V, I_{C} = 0, f = 1.0MHz$ 8.0	рF
$V_{CB} = 5.0V, I_{E} = 0, f = 1.0MHz$ 4.0	рF

ELECTRICAL CHARACTERISTICS (Continued)

SYMBOL	TEST CONDITIONS	MIN	MAX	<u>UNITS</u>
^t d	$V_{CC} = 10V, V_{BE(OFF)} = 2.0V, I_{C} = 100mA, I_{B1} = 10mA$		8.0	ns
t _r	$V_{CC} = 10V$, $V_{BE(OFF)} = 2.0V$, $I_{C} = 100$ mA, $I_{B1} = 10$ mA		15	ns
t _S	$V_{CC} = 10V$, $I_C = 10mA$, $I_{B1} = I_{B2} = 10mA$		20	ns
t _f	$V_{CC} = 10V$, $I_C = 100mA$, $I_{B1} = I_{B2} = 10mA$		15	ns
t _{on}	$V_{CC} = 3.0V$, $V_{BE(OFF)} = 1.5V$, $I_{C} = 10mA$, $I_{B1} = 3.0mA$		25	ns
t _{off}	$V_{CC} = 3.0V$, $I_C = 10mA$, $I_{B1} = 3.0mA$, $I_{B2} = 1.5mA$		35	ns
o_T	$V_{CC} = 3.0V$, $I_C = 10mA$, $I_B = 1.0mA$		80	рC



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OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- · Inventory bonding
- · Consolidated shipping options

- · Custom bar coding for shipments
- · Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- · Custom electrical curves
- · Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- · Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- · Custom product and package development

REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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